

STTH200L06TV

Turbo 2 ultrafast high voltage rectifier

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses

Description

The STTH200L06TV, which is using ST Turbo 2 600 V technology, is specially suited for use in switching power supplies, and industrial applications (such as welding), as rectification diode.

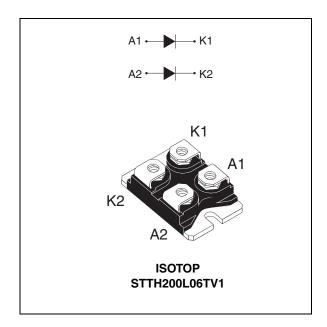


Table 1. Device summary

Symbol	Value
I _{F(AV)}	Up to 2 x 120 A
V_{RRM}	600 V
T _j	150 °C
V _F (typ)	0.95 V
t _{rr} (max)	80 ns

TM: ISOTOP is a trademark of STMicroelectronics

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Characteristics 1

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit			
V _{RRM}	Repetitive peak reverse voltage	600	V			
I _{F(RMS)}	Forward rms current	Forward rms current				
	Average forward current S = 0.5	T _c = 65 °C	Per diode	100	Α	
IF(AV)	Average forward current, $\delta = 0.5$	T _c = 35 °C	Per diode	120	Α	
I _{FSM}	Surge non repetitive forward current	800	Α			
T _{stg}	Storage temperature range	-55 to + 150	°C			
Tj	Maximum operating junction temperatur	150	°C			

Table 3. Thermal parameter

Symbol	Parameter	Maximum	Unit	
В	lunation to coop	Per diode	0.60	
R _{th(j-c)}	Junction to case	Total	0.35	°C/W
R _{th(c)}	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} x R_{\text{th(j-c) (per diode)}} + P_{\text{(diode2)}} x R_{\text{th(c)}}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V - V			100	μA
'R`	In the verse leakage current	T _j = 125 °C	$V_R = V_{RRM}$		100	1000	μΛ
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 100 A			1.55	V
		T _j = 150 °C			0.95	1.20	V

^{1.} Pulse test: t_p = 5 ms, δ < 2 %

To evaluate the maximum conduction losses use the following equation: P = 0.93 x $I_{F(AV)}$ + 0.0027 $I_{F}^{2}(RMS)$

$$P = 0.93 \times I_{F(AV)} + 0.0027 I_{F}^{2}_{(BMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

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Table 5. Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	Reverse recovery	T _i = 25 °C	$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_R = 1 \text{ A}$			80	ns
t _{rr}	time	1 _j = 25 C	$I_F = 1 \text{ A}, \ dI_F/dt = 50 \text{ A/}\mu\text{s}, \ V_R = 30 \text{ V}$		85	120	115
I _{RM}	Reverse recovery current	T _j = 125 °C	$I_F = 100 \text{ A}, dI_F/dt = 400 \text{ A}/\mu\text{s}, \\ dI_F/dt = 100 \text{ A}/\mu\text{s}$		15	20	Α
t _{fr}	Forward recovery time	T _j = 25 °C	$I_F = 100 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$			700	ns
V _{FP}	Forward recovery voltage	T _j = 25 °C	$I_F = 100 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$		3.4		V

Figure 1. Conduction losses versus average Figure 2. Forward voltage drop versus forward current (per diode) forward current (per diode)

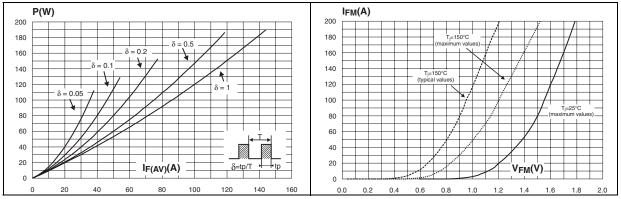
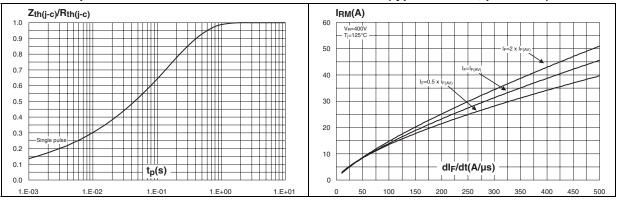


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values, per diode)



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Figure 5. Reverse recovery time versus dl_F/dt Figure 6. Reverse recovery charges versus dl_F/dt (typical values, per diode)

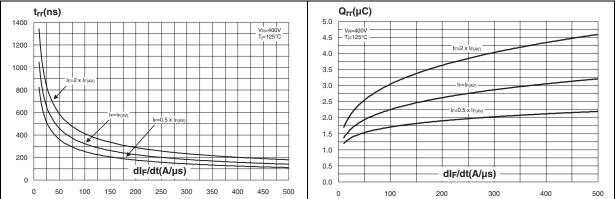


Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)

Figure 8. Relative variations of dynamic parameters versus junction temperature

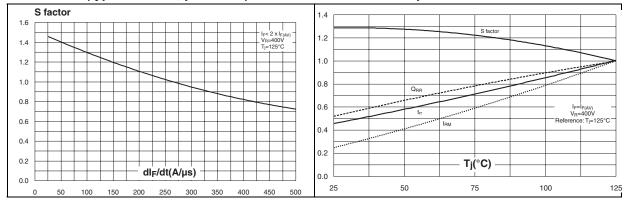
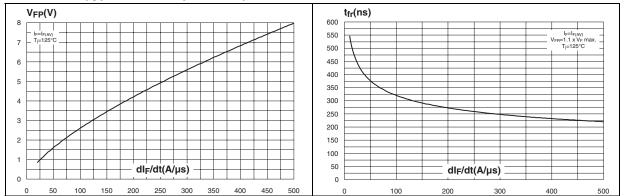


Figure 9. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

Figure 10. Forward recovery time versus dI_F/dt (typical values, per diode)

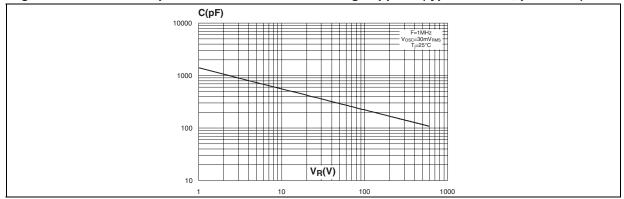


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Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)

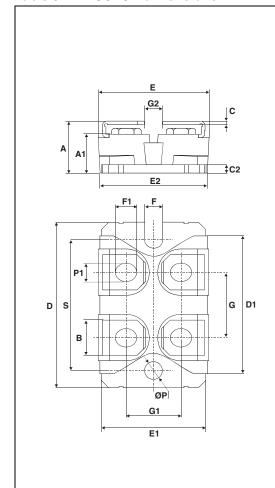


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 6. ISOTOP dimensions



		Dimer	nsions	
Ref.	Millim	neters	Inc	hes
	Min.	Max.	Min.	Max.
Α	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
В	7.8	8.20	0.307	0.323
С	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
Е	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.97	6 typ.
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
Р	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH200L06TV1	STTH200L06TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
07-Sep-2004	1	First issue.
05-Sep-2011	2	Updated Figure 6.

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